

## EAST Search History

### EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S87	179	(sin OR Si3N4 or "Si.sub.3 N.sub.4" or (Silicon adj nitride)) with plasma with CVD with ((resistivity or resistance) or semi\$1nsulat\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/13 12:39
S86	62	S85 and @pd>"20090801"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:41
S85	1492	257/409,488-490.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:41
S84	16	S83 and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:41

S83	140	(Yano near Mitsuhiro) or (Mochizuki near Kouichi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:41
S82	227	S81 and (sin OR SiN or "Si.sub.3 N.sub.4" or si3N4 or (Silicon adj nitride)) and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:32
S81	1202	(termination or peripheral) with (field adj4 (relie \$6 or relax\$6 or plate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:32
S80	90	257/e29.01,e29.006.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:20
S73	227	S72 and @pd>"20090801"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 22:58

S72	4272	257/139,212,34,401,630,646,649.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 22:58
S69	188	S66 and (sin OR (SILIcon adj nitride)) and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:37
S68	1	S66 and S67	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:36
S67	11850	(sin OR (SILIcon adj nitride)) with plasma with CVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:36
S66	1105	(termination or peripheral) with (field adj4 (relie \$6 or relax\$6 or plate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:36

S65	14	257/e29.01, e29.S49.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:34
S64	117	S61 not S62	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:31
S63	11	"5196354"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:26
S62	16	S61 and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:21
S61	133	(Yano near Mitsuhiro) or (Mochizuki near Kouichi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:21

S60	196	S59 and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:09
S59	444	(sin OR (SILIcon adj nitride)) with termination	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:09
S58	1	(sin OR (SILIcon adj nitride)) with plasma with CVD with termination	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:09
S57	18	"S521409"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:04
S56	424	S54 and S55	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:39

S55	5802	(sin OR (SILIcon adj nitride)) with (terminat\$6 or peripheral)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:39
S54	4562	S53 and gate and (terminat\$6 or peripheral)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:38
S53	11850	(sin OR (SILIcon adj nitride)) with plasma with CVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:37
S52	17	S51 and terminat\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:32
S51	154	(sin OR (SILIcon adj nitride)) with plasma with CVD with ((resistivity or resistance) or semi \$1insulat\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:32

S50	15	(sin OR (SILIcon adj nitride)) with plasma with CVD with (terminat\$6)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:31
S49	1702023	(sin OR (SILIcon adj nitride)) with plasma with CVD (terminat\$6)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:31
S48	332	S47 and @pd>"20081001"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18
S47	5875	S44 or S45 or S46	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18
S46	1430	257/409,488-490.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18

S45	755	257/339.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18
S44	4054	257/139,212,34,401,630,646,649.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18

6/16/2010 10:22:26 PM

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